JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

SOT-363 Plastic-Encapsulate Diodes

BAV199DW Multi-Chip DIODES

SOT-363

FEATURES

Power dissipation

$P_{CM:}$ 0.2 W (Tamb=25℃)

Collector current

I_F : 200 mA

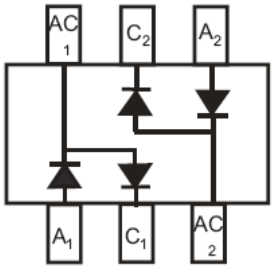
Collector-base voltage

V_R : 85 V

Operating and storage junction temperature range

T_J,T_{stg}: -55℃ to +150℃

MARKING:K52



ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Reverse breakdown voltage	$V_{(BR)R}$	I_R= 100μA	85			V
Reverse voltage leakage current	I_R	V_R=75V			5	nA
Forward voltage	V_F	I_F=1mA I_F=10mA I_F=50mA I_F=150mA			0.9 1.0 1.1 1.25	V
Junction capacitance	C_j	V_R=0V f=1MHz		2		pF
Reveres recovery time	t_{rr}	I_F=I_R=10mA I_{rr}=0.1XI_R R_L=100Ω			3	nS

Typical Characteristics

BAV199DW

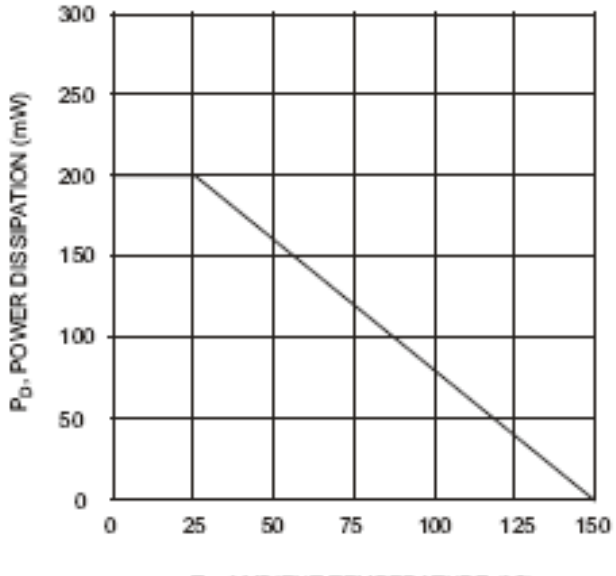


Fig. 1 Power Derating Curve

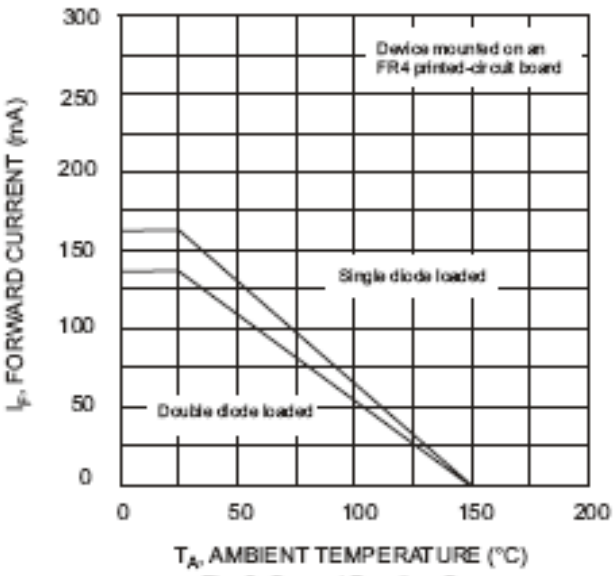


Fig. 2 Current Derating Curve

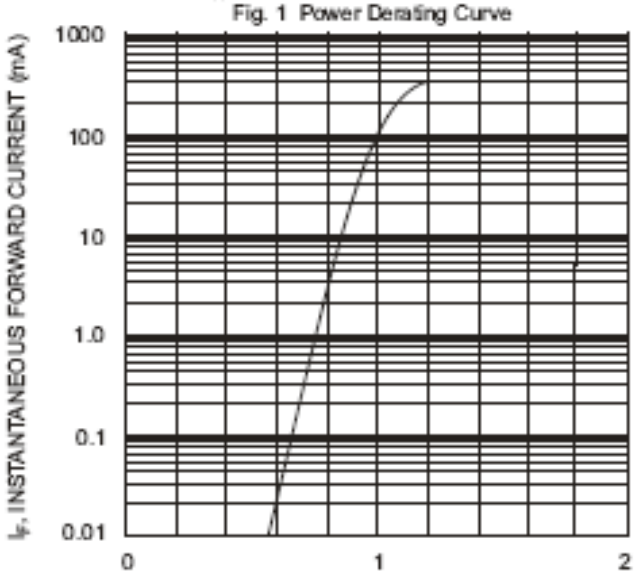


Fig. 3 Typical Forward Characteristics

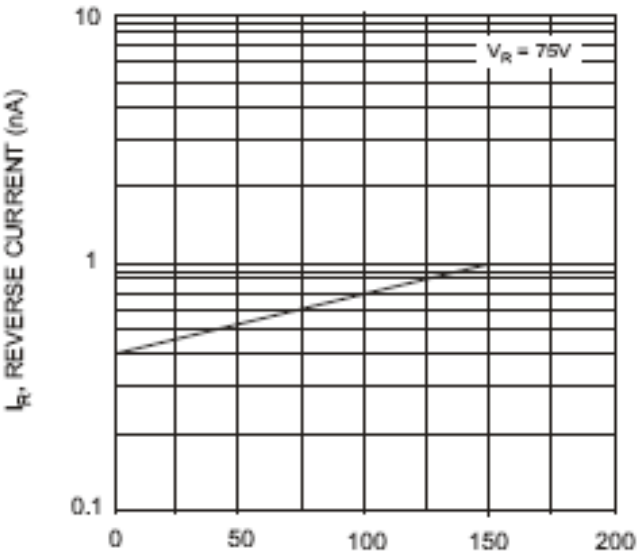


Fig. 4 Typical Reverse Characteristics